

Role of CF4 in gas amplification in gems

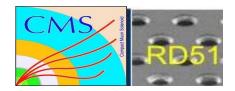
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(For Gems for CMS collaboration)

RD-51 mini week, November 2011



Outline

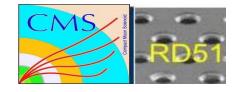


 A bit of discussion on CF₄
Gain in case of single gems for CF₄ mixtures

Loss rates in case of single gems

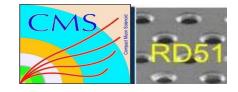
Gain in triple gem and comparison with data

The Gas called "CF₄"

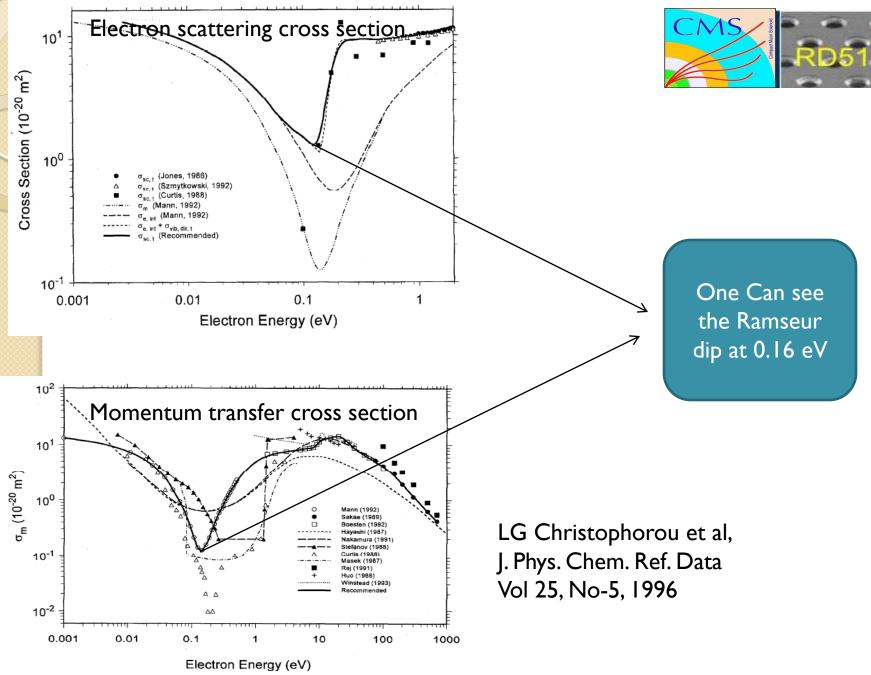


- A Fast gas because of large electron scattering cross-section > 0.5 eV. This lowers the energy of the electrons in the mixture to less than 0.5 eV. (Effectively acting like a pillow rather than a hard surface)
- At this energy the cross-section is less in case of Argon.
- Hence the mean free path is large, and so an increase in drift velocity over a range of E/p values.

The Gas called "CF₄"



- > 4 fundamental vibrational modes
 - Symmetric stretch (0.112 eV), symmetric bend (0.054 eV)
 - Asymmetric stretch, (0.157 eV) Asymmetric bend (0.078 eV)
 - Studies have revealed strong vibrational excitation by electron impact below 2.0 eV. (We know it is a fast gas !)
- Excitation energy of asymmetric stretch very near the Ramseur minimum in momentum and electron scattering crosssection at 0.16 eV.

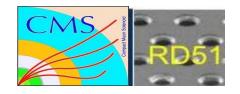




Attachment in CF₄

 $CF_{A}^{-} \rightarrow F^{-} + CF_{3}$

 $CF_4^- \rightarrow F_4 + CF_3^-$



- Resonant electron attachment to CF₄ occurs mainly in 6-8 eV via two negative ion states.
- > Ground state of CF_4^- at 6.8 eV producing F^- and CF_3^- via complementary channels.

F atoms

produced

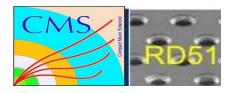


First electronically excited state of CF_4^{*-} at 7.6 eV producing only F^- .

$$CF_4^{*-} \rightarrow F^- + CF_3^{*}$$

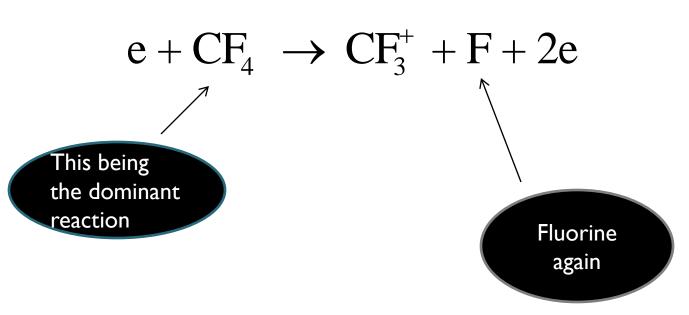
> An interesting thing to note is that $CF_4^$ not observed in gas phase as, only seen in van der waals clusters of CF_4 , where auto-detachment is slow.



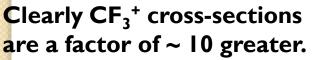


Ionization Of CF₄

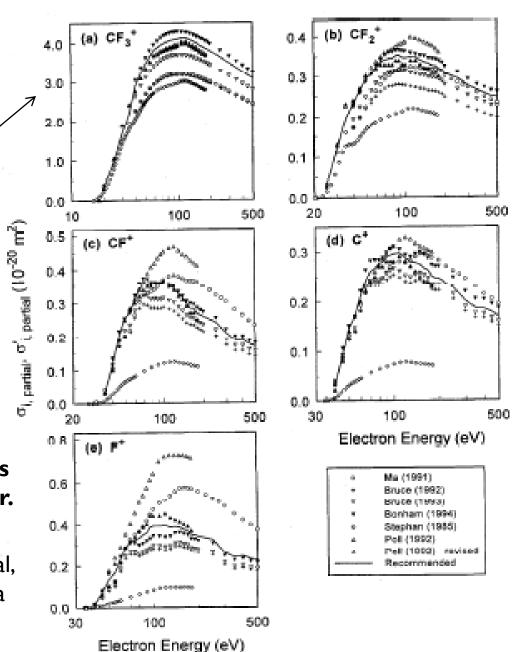
Dissociative Ionisation – dominant in CF_4 above 30-35 eV.



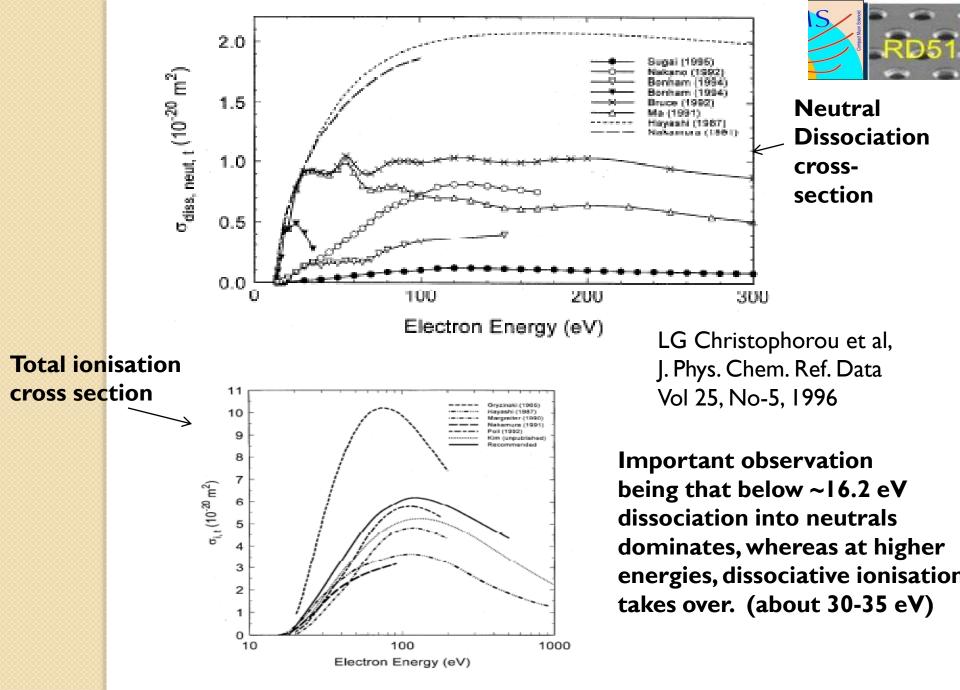
A look at the partial ionization cross section For production of CF_3^+ and other radicals !



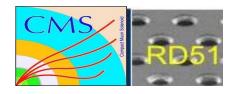
LG Christophorou et al, J. Phys. Chem. Ref. Data Vol 25, No-5, 1996



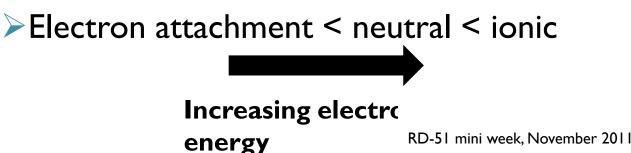
CMS/

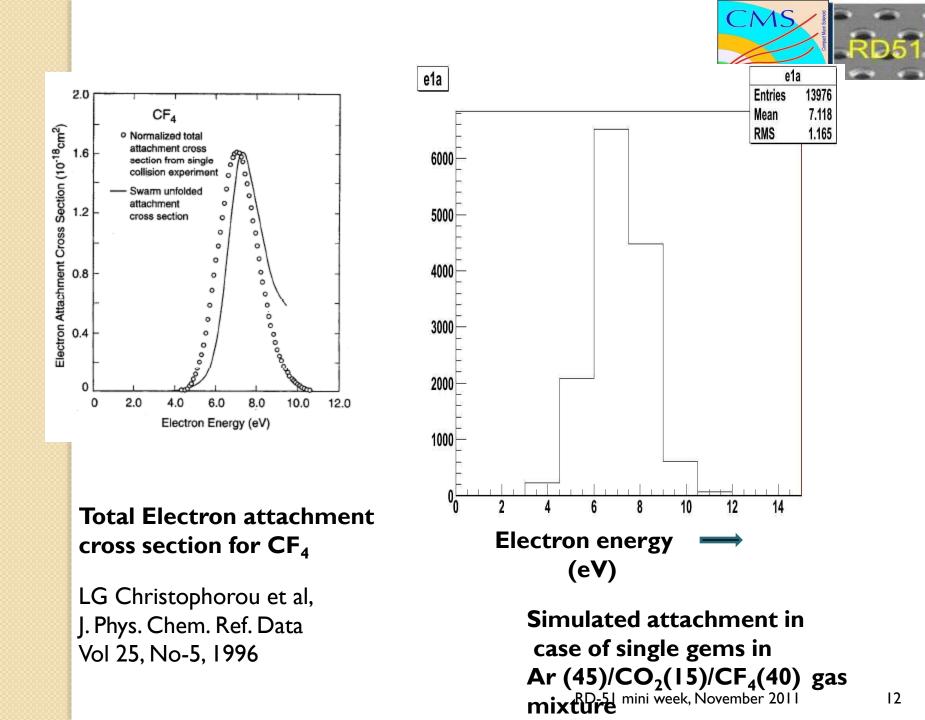


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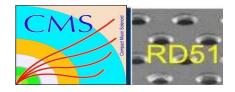


- The threshold for generating neutral fragments is about 12.5 eV.
- This value being lower than the ionization potential of CF₄ (16.2 eV), neutral dissociation dominant at low electron energies.
- At energies below neutral dissociation threshold, dissociation occurs via electron attachment.
- > So





Penning transfer?

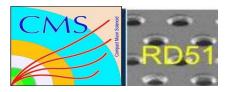


- Looks unlikely from the preceding discussion.
 - High ionization energy of 16.2 eV, which is also higher than the ionization energy of Argon !
 - > Hopefully no penning transfer from Ar to CF_4 .
 - \succ No stable excited state of CF₄
 - > So penning transfer from CF_4 to CO_2 unlikely

> Any data for CF_4 in single gems?

As a conclusion, we can take home the fact that gain should be lower in case of CF₄ mixture

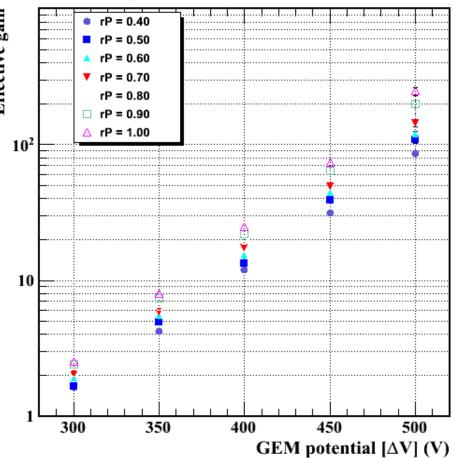
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Single gem plots $(Ar(45)/CO_2(15)/CF_4(40))$

The effective gain in case of single gem for $Ar/CO_2/CF_4$ mixture is shown for varying gem potentials and penning parameters.

- The parameters in simulation being
 - Drift field 2 kV/cm
 - Induction field 3 kV/cm
 - Drift /induction space 3/2 mm

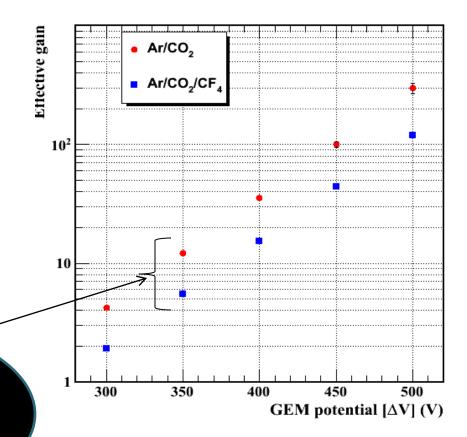




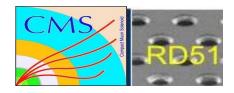
Comparison of effective gains

The value of gain in $Ar/CO_2/CF_4$ is compared with $Ar(70)/CO_{2}(30)$ (which compares well with the data) The penning parameter chosen is 0.6.

Clearly one can see a reduction of in gain in case of CF₄ mixture

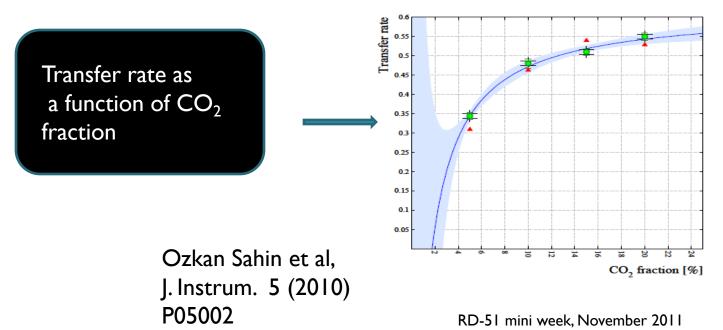


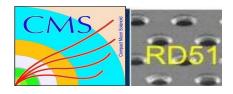
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Possible reasons

- Less Argon would mean less ionization electrons and less CO₂ which would mean less penning transfer.
- > Also presence of both CO_2 and CF_4 would lead to an increase in attachment loss.

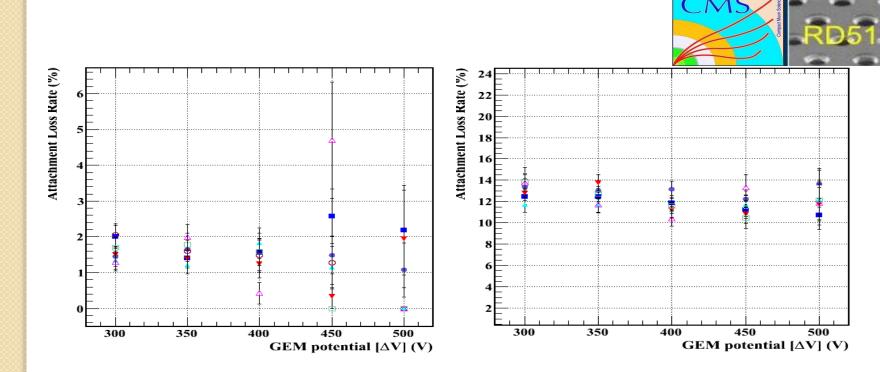




The loss rate plots for both the primary and secondary electrons are shown as :

- Attachment loss rate
- Geometric loss rate
- Overall loss rate

The values of the loss rate are compared with Ar/CO₂ mixture.

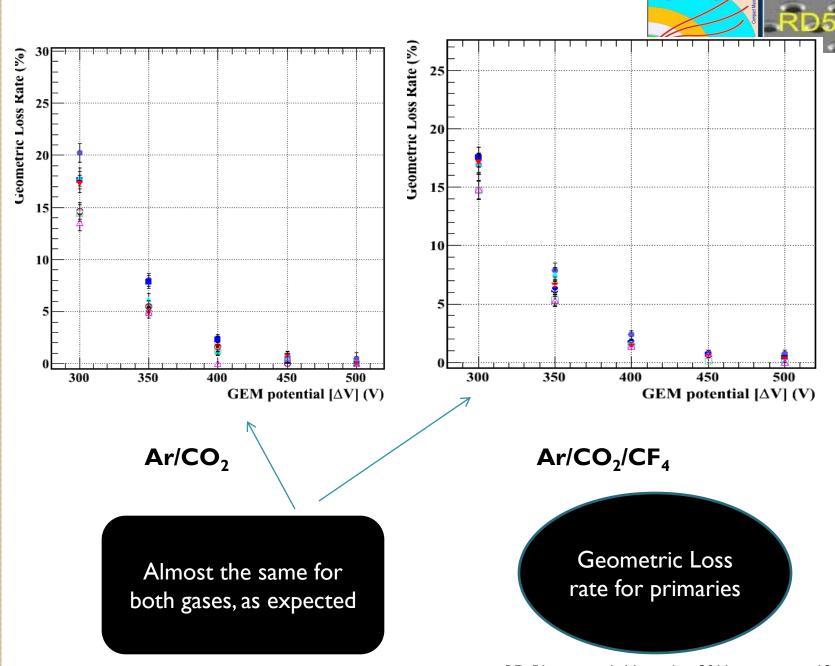


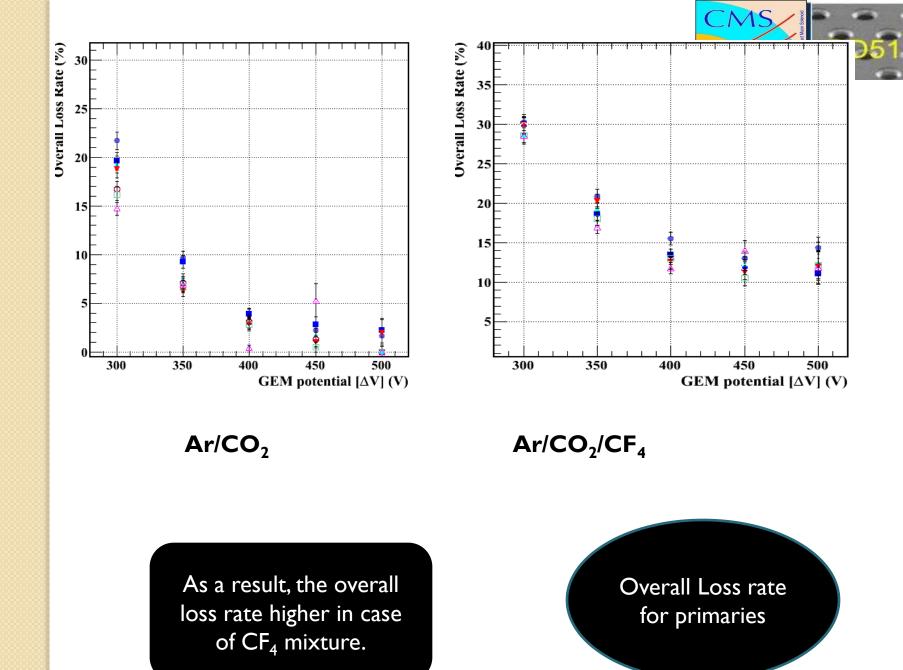
Ar/CO₂

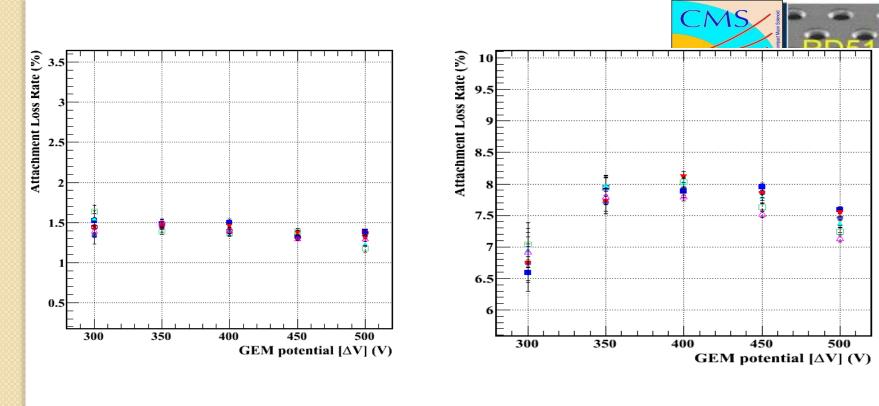
Ar/CO₂/CF₄

A much higher value seen in CF₄ mixture (About a factor of 6-7 higher)







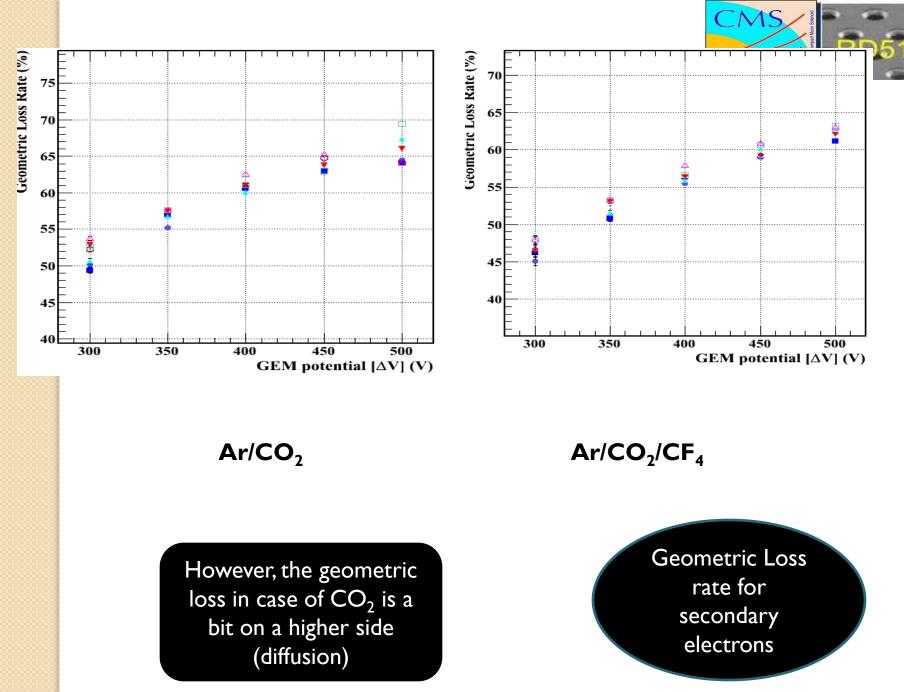


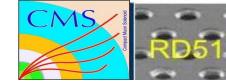
Ar/CO₂

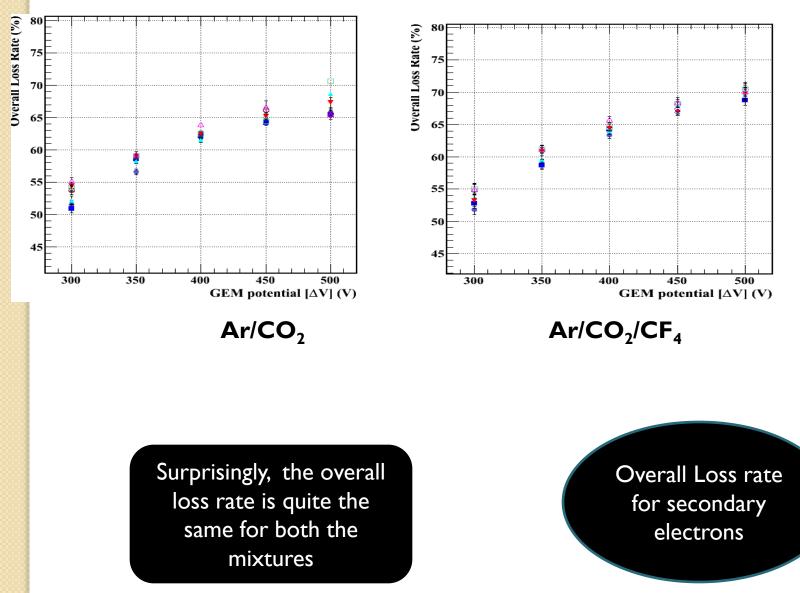
 $Ar/CO_2/CF_4$

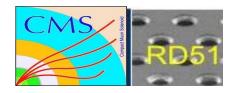
Attachment rate for secondary electrons higher in case of CF₄ mixture.



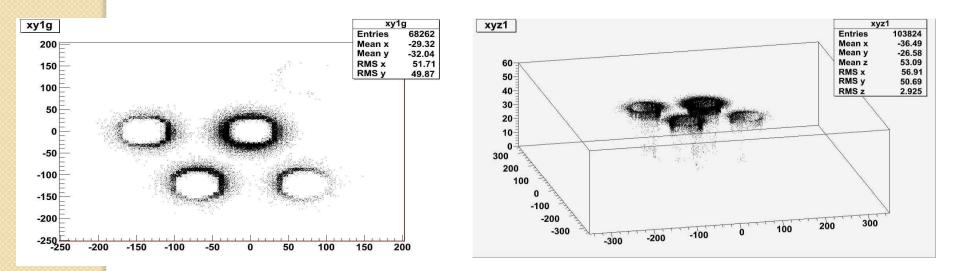








 Plotting the electron endpoints in the gem, gives us a good picture of the geometric loss in gems.



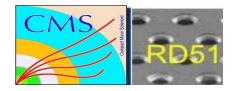
X-Y profile



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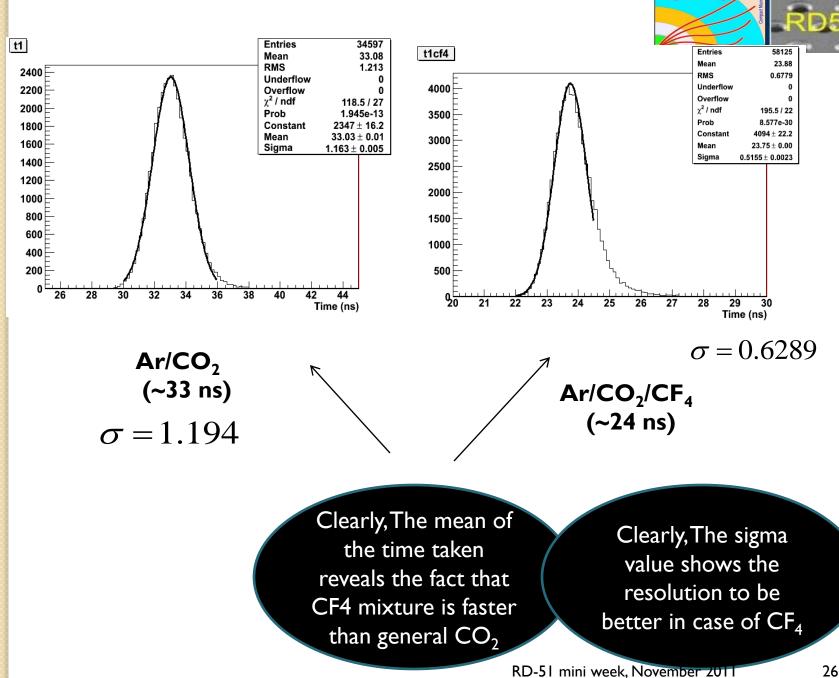


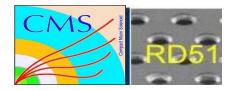
So how fast?



Plotting the time taken by the electrons to reach the anode in case of Ar/CO₂ and comparing the result with Ar/CO₂/CF₄ should give an indication.

> We fit it with a Gaussian function to get an estimate of the time resolution !





Triple gem

The gap for the triple gem were :

Drift space : 3 mm

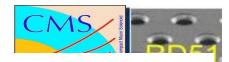
Transfer-1 space : 1 mm
Transfer-2 space : 2 mm

Induction space : I mm

The value of the various fields and potentials were taken from the group.

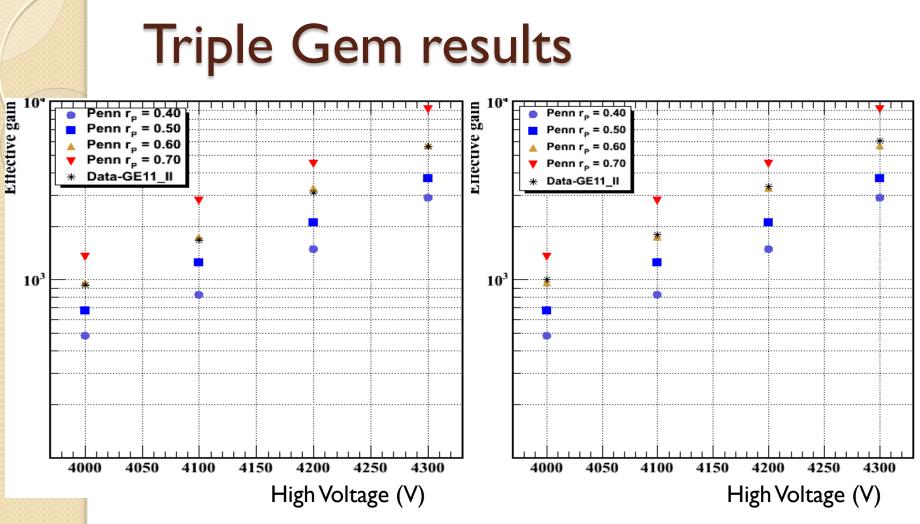
Gas mixture was Ar(45)/CO₂(15)/CF₄(40) ាំ

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However we divided the triple gem into three separate single gems, and then multiplied the gain in these three single gems to get the total gain

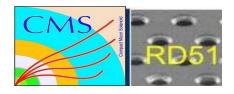
$$\mathbf{G}_{\mathrm{Total}} = \mathbf{G}_1 \times \mathbf{G}_2 \times \mathbf{G}_3$$



I layer Cu tape

2 layer Cu tape

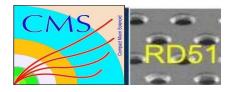
 The simulated gain seems to be in good agreement with the experimental gain. (Laura/ Michal/Andrey)



- The simulated gain matches quite well for penning parameter of 0.60.
- The transfer rate is 0.55 for 15 % CO₂ from Ozkan's paper. So we are in good shape ! (No role played by CF₄ in penning transfer)

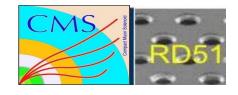


BUT...



- However when we simulate the gain in a triple gem structure, we are off-track !
- As an example, for HV supply of 4200, we get a value of ~ 1000 which is less compared to the experimental value of ~3000.
- Hopefully, we will get it sorted out !

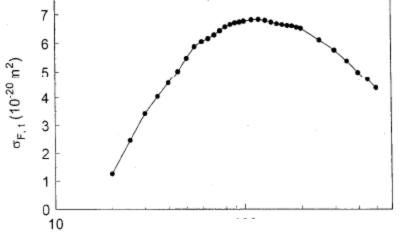
Dangers of Using CF₄

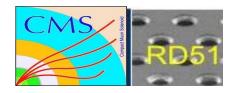


- CF₄ is an active source of reactive neutral and ionic fragment atoms and molecules (especially neutral F atoms)
- Neutral F atoms are active species in etching process.
- >Hopefully they don't eat the detector !

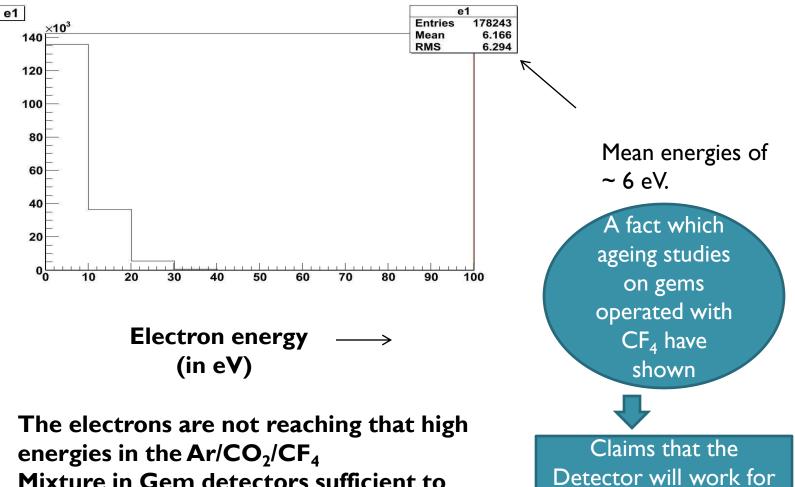
Cross-section for production of fluorine on impact of electron with CF₄

> LG Christophorou et al, J. Phys. Chem. Ref. Data Vol 25, No-5, 1996



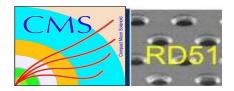


However ...



Mixture in Gem detectors sufficient to Produce enough fluorine to damage the detector that fast !

10 years





I would like to thank Rob Veenhof, Heinrich Schindler, Tania Moulik and Stefano Colafranceschi for their help

I would also like to thank RD51 for their support